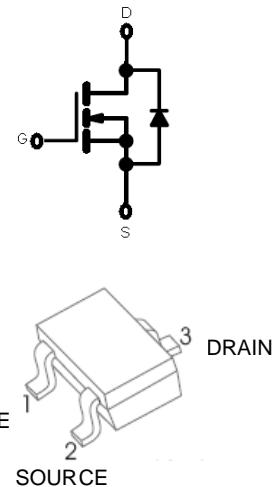




迈拓电子  
MAITUO ELECTRONIC

## MT2102 N-Channel MOSFET

V <sub>(BR)DSS</sub>	R <sub>DS(on)MAX</sub>	I <sub>D</sub>
20V	68mΩ@4.5V	2.1A
	115mΩ@2.5V	



### FEATURE

- TrenchFET Power MOSFET

### APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

SOT-323

### MARKING TS2

Maximum ratings (T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±8	
Continuous Drain Current	I <sub>D</sub>	2.1	A
Continuous Source-Drain Current(Diode Conduction)	I <sub>S</sub>	0.6	
Power Dissipation	P <sub>D</sub>	0.2	W
Thermal Resistance from Junction to Ambient (t≤5s)	R <sub>θJA</sub>	625	°C/W
Operation Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 ~ +150	°C



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## MOSFET ELECTRICAL CHARACTERISTICS

T<sub>a</sub>=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10µA	20			V
Gate-threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50µA	0.65	0.95	1.2	
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±8V			±100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V			1	µA
Drain-source on-resistance <sup>1</sup>	R <sub>DSS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.6A		0.059	0.068	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.1A		0.070	0.115	
Forward transconductance <sup>1</sup>	g <sub>f</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 3.6A		8		S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.94A, V <sub>GS</sub> = 0V		0.76	1.2	V
<b>Dynamic Characteristics</b>						
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.6A		4.0	10	nC
Gate-source charge	Q <sub>gs</sub>			0.65		
Gate-drain charge	Q <sub>gd</sub>			1.5		
Input capacitance <sup>2</sup>	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		300		pF
Output capacitance <sup>2</sup>	C <sub>oss</sub>			120		
Reverse transfer capacitance <sup>2</sup>	C <sub>rss</sub>			80		
<b>Switching Characteristics<sup>2</sup></b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10V, R <sub>L</sub> = 5.5Ω, I <sub>D</sub> ≈ 3.6A, V <sub>GEN</sub> = 4.5V, R <sub>G</sub> = 6Ω		7	15	ns
Rise time	t <sub>r</sub>			55	80	
Turn-off delay time	t <sub>d(off)</sub>			16	60	
Fall time	t <sub>f</sub>			10	25	

### Notes :

1. Pulse Test : Pulse width ≤ 300µs, duty cycle ≤ 2%.

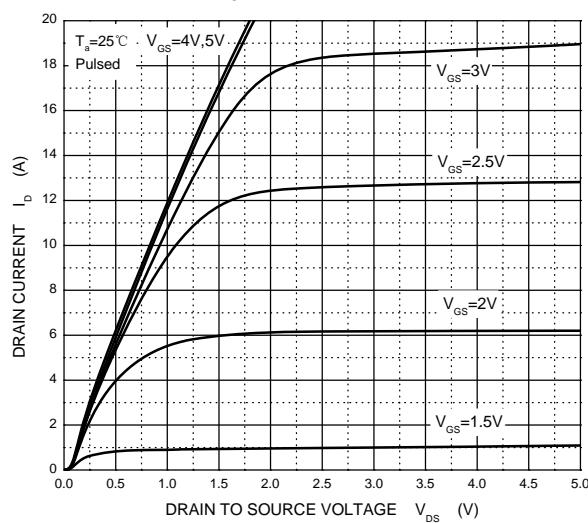
2. These parameters have no way to verify.



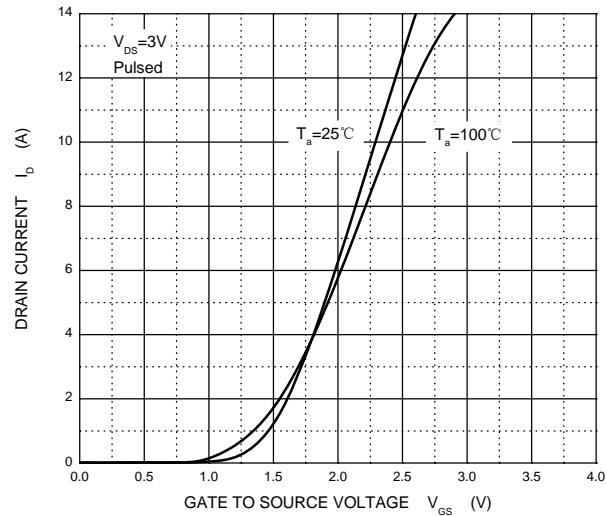
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## Typical Characteristics

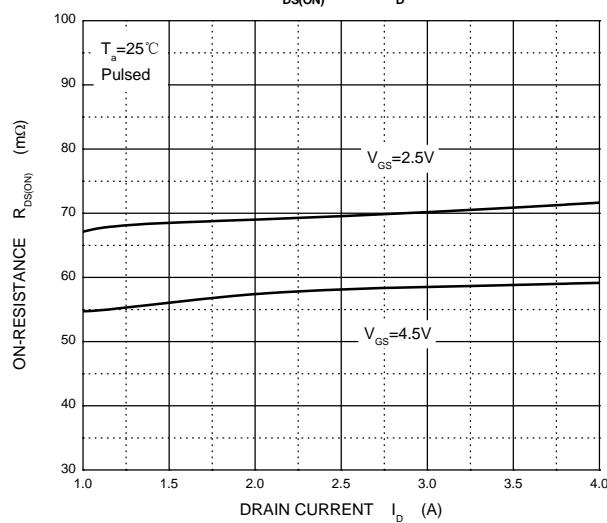
Output Characteristics



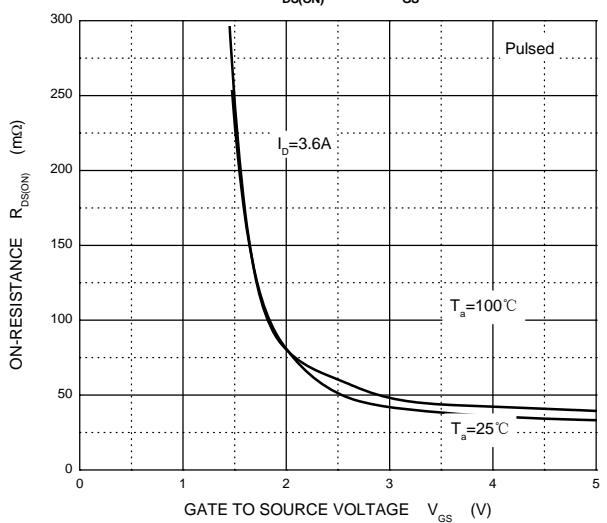
Transfer Characteristics



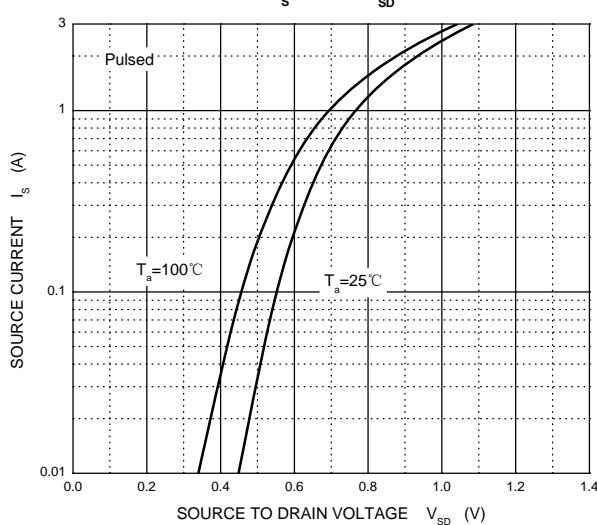
$R_{DS(ON)}$  ——  $I_D$



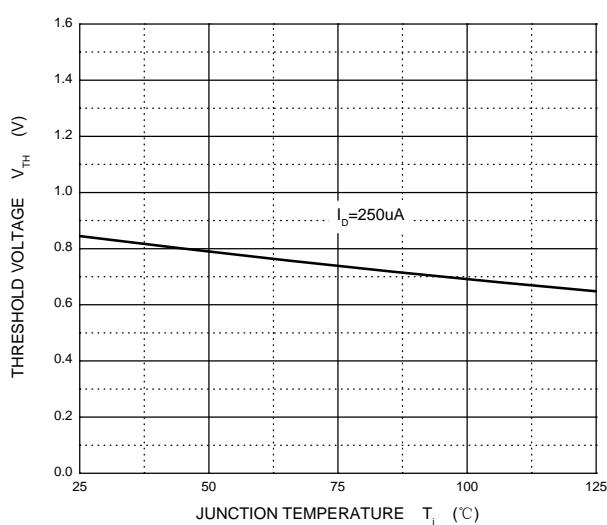
$R_{DS(ON)}$  ——  $V_{GS}$



$I_S$  ——  $V_{SD}$



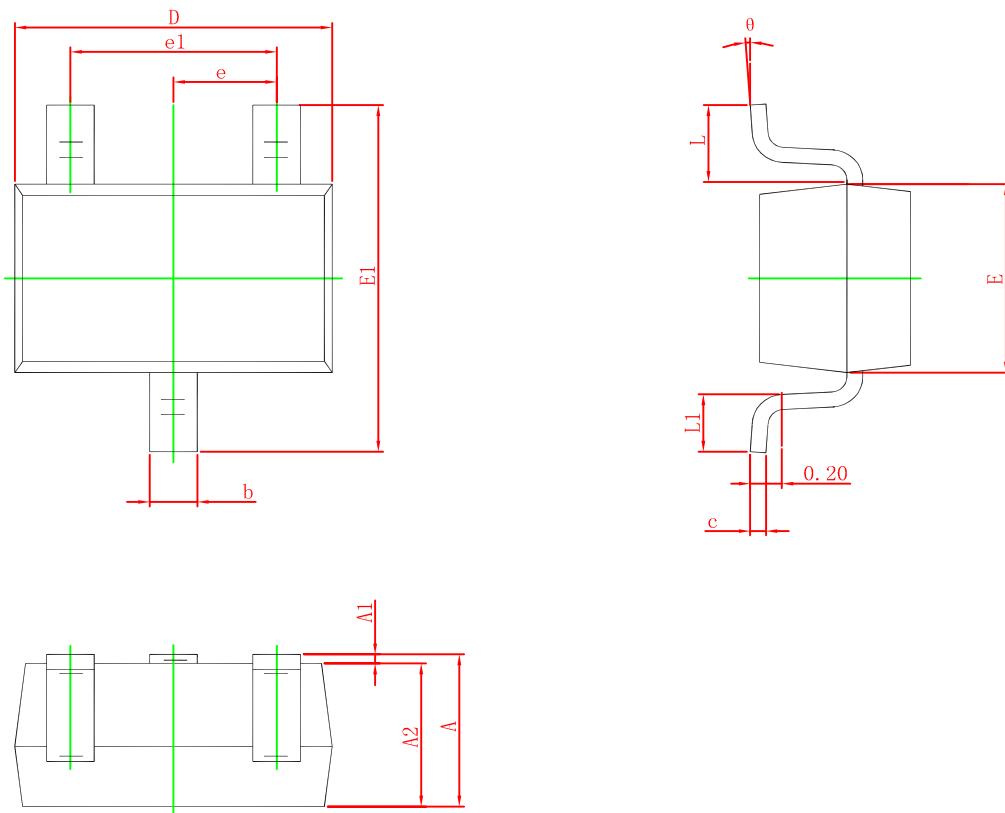
Threshold Voltage





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SOT-323 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°